	Туре	L	#	Hits	Search Text	DBs	Time Stamp	Comment
	BRS	<u> </u>		4	ng near kan-yin.in.	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/12/2 9 16:16	
2	BRS	L2		3		USPA T; US-P GPUB; FPO; JPO; DERW ENT; IBM_ TDB	2003/12/2 9 16:18	
3	BRS	L3			hensiek near stephen.in.	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/12/2 9 16:21	
4	BRS	L4			albrecht near peter.in.	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/12/2 9 16:19	

	Туре	L	# Hits	Search Text	DBs	Time Stamp	Comment
5	BRS	L5	2	4 and wax	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/12/2 9 16:20	
6	BRS	L6	579	510/175.ccls.	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/12/2 9 16:20	
7	BRS	L7	1690	438/692.ccls.	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/12/2 9 16:22	
8	BRS	L8	:17 - 7 :	7 and (semiconductor or wafer or substrate) near25 (polish\$3)	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/12/2 9 16:23	

	Туре	L #	Hits	Search Text	DBs	Time Stamp	Comment s
9	BRS	L9	19	7 and (semiconductor or wafer or substrate) near25 (polish\$3) near25 (wax)	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/12/2 9 16:30	
10	BRS	L10	409	(semiconductor or wafer or substrate) near25 (polish\$3) near25 (wax)	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/12/2 9 16:30	
11	BRS	L11	6	(semiconductor or wafer or substrate) near25 (polish\$3) near25 (wax) near25 (damage)	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/12/2 9 16:32	
12	BRS	L12	1	(bladder) near25 (polish\$3) near25 (wax) near25 (damage)	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/12/2 9 16:33	

	Туре	L #	Hits	Search Text	DBs	Time Stamp	Comment
13	BRS	L13	1	(backside or back near side) near25 (polish\$3) near25 (wax) near25 (damage)	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/12/2 9 16:33	
14	BRS	L14	1918	(backside or back near side) near25 (polish\$3)	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/12/2 9 16:33	
15	BRS	L15	74	(backside or back near side) near25 (polish\$3) near20 (air)	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/12/2 9 16:34	
16	BRS	L17	1	(backside or back near side) near25 (polish\$3) near20 (air) near50 (wafer) near25 (damage)	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/12/2 9 16:34	

	Туре	L	#	Hits	Search Text	DBs	Time Stamp	Comment
17	BRS	L.1	6	48	(backside or back near side) near25 (polish\$3) near20 (air) near50 (wafer)	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/12/2 9 16:39	
18	BRS	L1	9	2	(backside or back near side) near25 (polish\$3) near20 (air) near50 (wafer or substrate) near25 (wax\$3)	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/12/2 9 16:45	
19	BRS	L1	8	68	(backside or back near side) near25 (polish\$3) near20 (air) near50 (wafer or substrate)	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/12/2 9 16:47	
20	BRS	L2(D	7973	(front near side) near15 (wafer or substrate)	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/12/2 9 16:47	

	Туре	L #	Hits	Search Text	DBs	Time Stamp	Comment
21	BRS	L21		(front near side) near15 (wafer or substrate) near20 (polish\$3 near15 slurry)		2003/12/2 9 16:47	

	ט	1	PT	P	Document ID	Issue Date	Pages	Title
1	×				US 20030139067 A1	20030724	9	Water and method for storing silicon wafer
2					US 6530826 B2	20030311	9	Process for the surface polishing of silicon wafers
3					US 6491836 B1	20021210	14	Semiconductor wafer and production method therefor
4					US 6479386 B1	20021112	10	Process for reducing surface variations for polished wafer
5					US 6451696 B1	20020917		Method for reclaiming wafer substrate and polishing solution compositions therefor
6					US 6342166 B1	20020129	18	Method of detecting end point of polishing of wafer and apparatus for detecting end point of polishing
7					US 6338805 B1	20020115	8	Process for fabricating semiconductor wafers with external gettering

	U	1	PT	P	Document II	Issue Date	Pages	Title
8					US 6296717 B1	20011002	7	Regeneration of chemical mechanical polishing pads in-situ
9					US 6211089 B1	20010403	5	Method for fabricating GaN substrate
10					US 6028006 A	20000222	7	Method for maintaining the buffer capacity of siliceous chemical-mechanical silicon polishing slurries
11					US 6004866 A	19991221	13	Method for manufacturing bonded wafer and bonded wafer manufactured thereby
12					US 5893755 A	19990413		Method of polishing a semiconductor wafer
13					US 5814240 A	19980929		Method for polishing a semiconductor wafer
14				1 1 3	US 5770522 A	19980623	10	Polishing block heater
15				11:	US 5429711 A	19950704		Method for manufacturing wafer

	υ	1	PT	P	Document ID	Issue Date	Pages	Title
16				1)	US 5269876 A	19931214	17	Process for producing crystal article
17					US 4954141 A	19900904	6	Polishing pad for semiconductor wafers
18					US 4869779 A	19890926	7	Hydroplane polishing device and method
19				1 1 3	US 3629023 A	19711221		METHOD OF CHEMICALLY POLISHING CRYSTALS OF II(b)-VI(a) SYSTEM